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Inclosure Material: Metal **Overall Length:** 1.000 inches **Function For Which Designed:** Rectifier **End Application:** Low altitute navigation & targeting infrared system (lantirn) **Mounting Facility Quantity:** 1 **Mounting Method:** Threaded stud **Features Provided:** Burn in and hermetically sealed case **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 reverse voltage, peak **Current Rating Per Characteristic:** 300.00 amperes forward current, average preset Maximum Operating Tempurature Per Measurement Point: 125.0 degrees celsius ambient air **Special Features:** Weapon system essential; junction pattern arrangement: pn **Test Data Document:** 04939-717801309 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 pin Shelf Life: N/a Unit Of Measure: ---**Demilitarization:** No

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